

### PHOTO REFLECTOR

### **■ GENERAL DESCRIPTION**

The NJL5161K/5163K/5165K/5167 are super miniature and super thin photo reflectors, which consist of high output infrared emitting and high sensitve Si photo transistor.

### **■ FEATURES**

- Super miniature, super thin type
- Built-in visible light cut-off filter.
- High output, high S/N ratio.

### ■ APPLICATIONS

- End detector of video, audio tape.
- Rotation detection and control of various motors, audio turntables.
- Paper edge detection of facsimile printer, X-Y recorder.
- Reading out the characters of bar code reader, encorder and the auto-matic vending machine.
- Various detection of industrial system, such as FDD, Robot.

### ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Emitter			
Forward Current (Continuous)	IF	50	mA
Pulse Forward Current	. IFP	500(note 1)	mA
Reverse Voltage (Continuous)	V <sub>R</sub>	6	v
Power Dissipation	$P_{\rm D}$	75	mW
Detector			
Collector-Emitter Voltage	VCEO	25	v
Emitter-Collector Voltage	VECO	6	v
Collector Current	Ic	20	.mA
Collector Power Dissipation	Pc	75	mW
Coupled			
Total Power Dissipation	Ptot	100	mW
Operating Temperature	Topr	−20°C~+90	°C
Storage Temperature	T <sub>stg</sub>	$-30^{\circ}\text{C}\sim+100$	°C
Soldering Temperature	Tsol	260	°C
		(10sec. 1.5mm from body)	

(note 1): Pulsewidth≤10µs. Duty Ratio 0.01

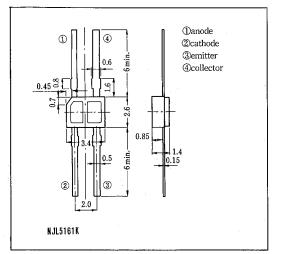
### **■ ELECTRO-OPTICAL CHARACTERISTICS** (Ta=25°C)

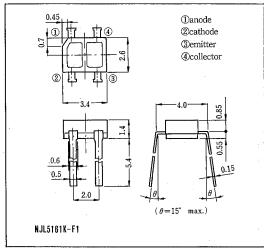
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Emitter						
Forward Voltage	$V_F$	$I_F = 4mA$	_	_	1.2	v
Reverse Current	$I_R$	$V_R = 6V$			1	μA
Capacitance	Ct	$V_R = 0V$ , $f = 1MHz$		25	_	рF
Detector						•
Dark Current	I <sub>CEO</sub>	V <sub>CE</sub> =20V		_	100	nA
Collector-Emitter Voltage	V <sub>CEO</sub>	$I_{C} = 100 \mu A$	25	l —	_	V
Emitter-Collector Current	I <sub>ECO</sub>	V <sub>ECO</sub> =6V	_	l —	100	μA
Coupled	i					,
Output Current	Io	$I_F = 4mA, V_{CE} = 2V, d = 0.7mm$	21		125	μA
Operating Dark Current	ICEOD	$I_F = 4mA$ , $V_{CE} = 2V$		l —	100	nA
Rise Time	t <sub>r</sub>	$V_{CE} = 2V$ , $I_F = 4mA$ , $R_L = 1k\Omega$ , $d = 0.7mm$		20	_ :	μs
Fall Time	tf	$V_{CE}=2V, I_F=4mA, R_L=1k\Omega, d=0.7mm$		20	_	μs

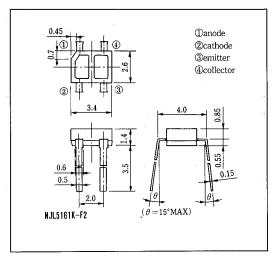
### **■ RANK OF OUTPUT CURRENT**

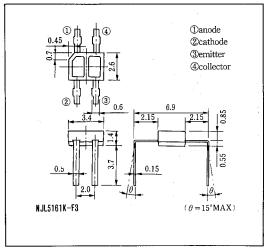
RANK	A	В	С
Ι <sub>Ο</sub> (μΑ)	60~125	35~73	21~43

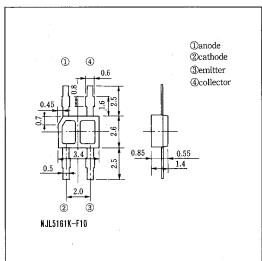
### ■ OUTLINE (typ.) Unit: mm

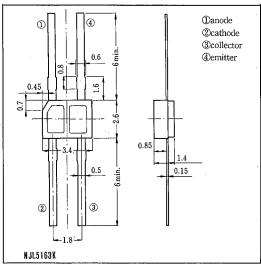




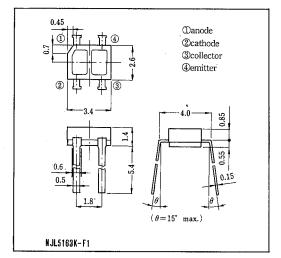


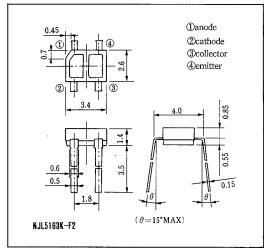


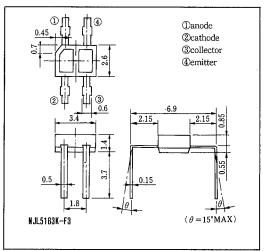


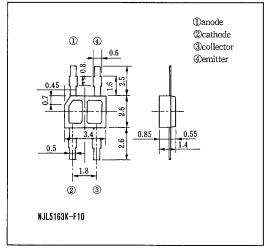


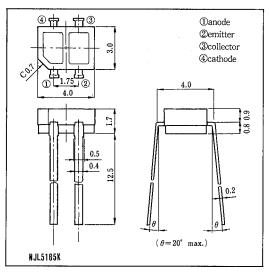
### ■ OUTLINE (typ.) Unit: mm

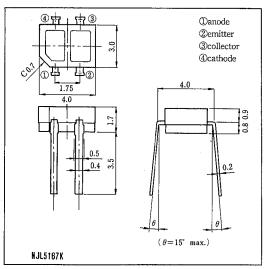








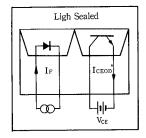


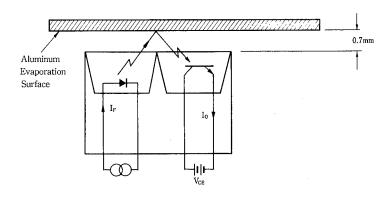


### **■ MEASURING SPECIFICATION FOR OUTPUT CURRENT**

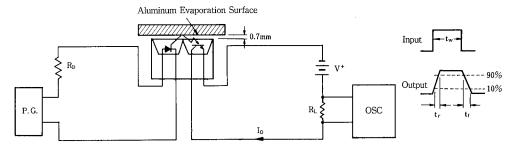
The output current can be measured when reflected at the aluminum

### ■ MEASURING CIRCUIT FOR OPERATING DARK CURRENT

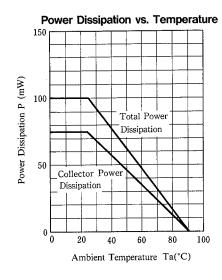


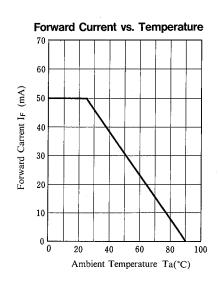


### **■ MEASURING CIRCUIT FOR RESPONSE TIME**

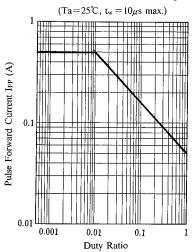


### ■ MAXIMUM RATING CURVES



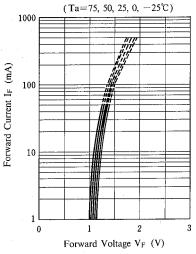


### Pulse Forward Current vs. Duty Ratio

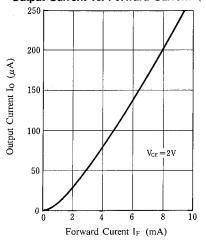


### TYPICAL CHARACTERISTICS

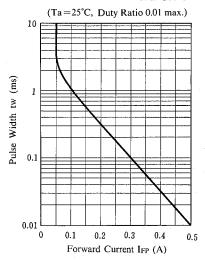
## Forward Current vs. Forward Voltage



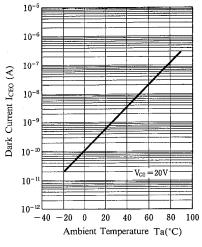
### Output Current vs. Forward Current (Ta=25°C)

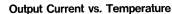


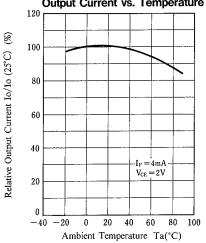
### Pulse Width vs. Forward Current



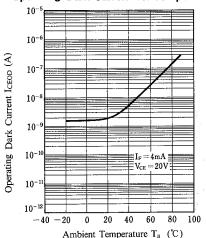
### Dark Current vs. Temperature

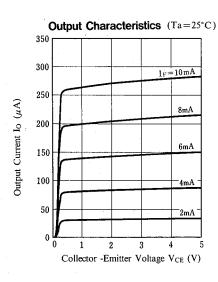


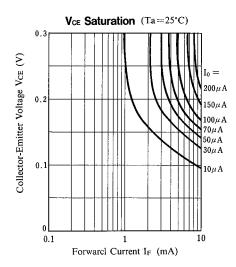


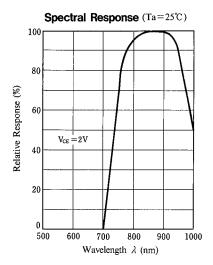


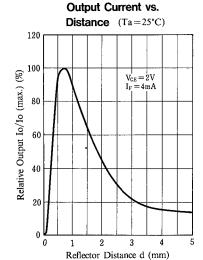
### Operating Dark Current vs. Temperature

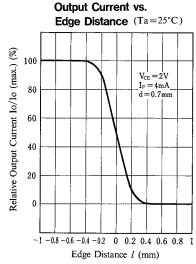






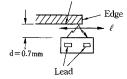


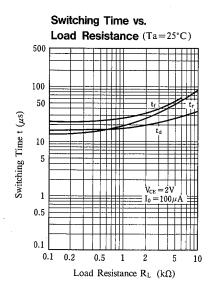


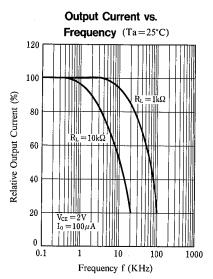


# ■ MEASURING SPECIFICATION FOR EDGE RESPONSE

Aluminum Evaporation Surface







### PRECAUTION FOR HANDLING

### 1. Soldering

1) Avoid the reflow method and the solder to touch the body of the device during wave soldering. This is to prevent changes in optical characteristics of the device.

2) Recommended in Soldering

Temperature

Time Lead

Soldering Position

260℃ maximum

less than 10 seconds

At least 1.5mm from body

- 3) Soldering is recommended to be done in as short period of the time as possible by controlling the temperature of the soldering iron or by the iron of less than 15 watts.
- 4) The resin gets softened right after soldered, so, the following care has to be taken.
  - Not to contact the lens surface to anything
  - Not to dip the device into water or any solvents
- 5) It is recommended not to solder when the leads or between the lead get pulled, depressed or twisted.
- 6) In the case of using rosin flux, be careful to avoid contact with the lens surface. If the lens is covered with the flux, the specified characteristics cannot be achieved.

### 2. Post Solder Cleaning

- 1) Organic solvents for flux removal like trichloroethlene, acetone, thinner etc, might attack the lens surface. It is preferable to use less reactive solvents, Methyl Alcohol, Isopropyle Alcohol.
- 2) Cleaning Operation

Cleaning Solvent Temperature: 35°C maximum

Dipping Time

: 3 minute maximum

### 3. Attention in handling

- 1) Treat not to touch the lens surface.
- 2) Avoid dust and any other foreign materials (flux, paint, bonding material, etc)on the lens surface.
- 3) Never to apply reverse voltage( $V_{EC}$ ) of more than 6V on the photo transistor when measuring the characteristics or adjusting the system. If applied, it causes to lower the sensitivity.
- 4) When mounting, special care has to be taken on the mounting position and tilting of the device because it is very important to place the device to the optimum position to the object.

### 4. Storage

The leads are silver plated and they are discolored if the device is left open to the air for long after taken out of the envelope. It causes deterioration of soldering characteristics. Mount the device as short as possible after opening the envelope.

## NJL5161K/63K/65K/67K

## **MEMO**

[CAUTION]
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